



**THE DATASHEET OF
DMB54D0UDW-7**



Features

- N-Channel MOSFET and PNP Transistor in One Package
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead, Halogen and Antimony Free, RoHS Compliant (Note 2)**
- **ESD Protected MOSFET Gate up to 2kV**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Alloy 42 lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.006 grams (approximate)


Maximum Ratings – MOSFET, Q1 @_{T_A} = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	50	V
Gate-Source Voltage	V _{GSS}	±12	V
Drain Current (Note 1) Continuous	I _D	160	mA
Pulsed Drain Current (Note 1)	I _{DM}	560	mA

Maximum Ratings - PNP Transistor, Q2 @_{T_A} = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current	I _C	-100	mA

Thermal Characteristics, Total Device @_{T_A} = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P _D	250	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. No purposefully added lead. Halogen and Antimony Free.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics - MOSFET @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Drain-Source Breakdown Voltage	BV _{DSS}	50	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	10	μA	V _{DS} = 50V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	1.0 5.0	μA	V _{GS} = ±8V, V _{DS} = 0V V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(th)}	0.7	0.8	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.1	4	Ω	V _{GS} = 4V, I _D = 100mA
		—	4	5		V _{GS} = 2.5V, I _D = 80mA
Forward Transconductance	g _{FS}	180	—	—	mS	V _{DS} = 10V, I _D = 100mA, f = 1.0KHz
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	25	—	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	5	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.1	—	pF	

Electrical Characteristics - PNP Transistor @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 4)	V _{(BR)CBO}	-50	—	—	V	I _C = 10μA, I _B = 0
Collector-Emitter Breakdown Voltage (Note 4)	V _{(BR)CEO}	-45	—	—	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage (Note 4)	V _{(BR)EBO}	-5	—	—	V	I _E = 1μA, I _C = 0
DC Current Gain (Note 4)	h _{FE}	220	290	475	—	V _{CE} = -5.0V, I _C = -2.0mA
Collector-Emitter Saturation Voltage (Note 4)	V _{CE(SAT)}	—	—	-100	mV	I _C = -10mA, I _B = -0.5mA
		—	—	-400		I _C = -100mA, I _B = -5.0mA
Base-Emitter Saturation Voltage (Note 4)	V _{BE(SAT)}	—	-700	—	mV	I _C = -10mA, I _B = -0.5mA
		—	-900	—		I _C = -100mA, I _B = -5.0mA
Base-Emitter Voltage (Note 4)	V _{BE(ON)}	-600	—	-750	mV	V _{CE} = -5.0V, I _C = -2.0mA
		—	—	-820		V _{CE} = -5.0V, I _C = -10mA
Collector-Cutoff Current (Note 4)	I _{CBO}	—	—	-15	nA	V _{CB} = -30V
		—	—	-4.0		V _{CB} = -30V, T _A = 150°C
Collector-Emitter Cut-Off Current (Note 4)	I _{CE(S)}	—	—	-100	nA	V _{CE} = -45V
Gain Bandwidth Product	f _T	100	—	—	MHz	V _{CE} = -5.0V, I _C = -10mA, f = 100MHz
Output Capacitance	C _{OB}	—	—	4.5	pF	V _{CB} = -10V, f = 1.0MHz
Noise Figure	NF	—	—	10	dB	I _C = -0.2mA, V _{CE} = -5.0Vdc, R _S = 2.0KΩ, f = 1.0KHz, BW = 200Hz

Notes: 4. Short duration pulse test used to minimize self-heating effect.

MOSFET

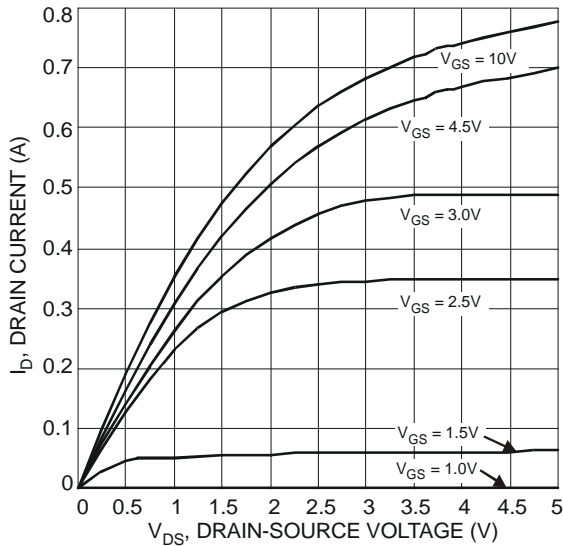


Fig. 1 Typical Output Characteristics

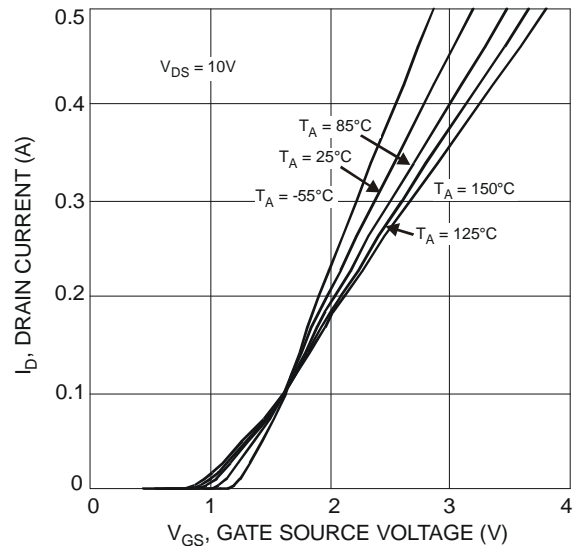


Fig. 2 Typical Transfer Characteristics

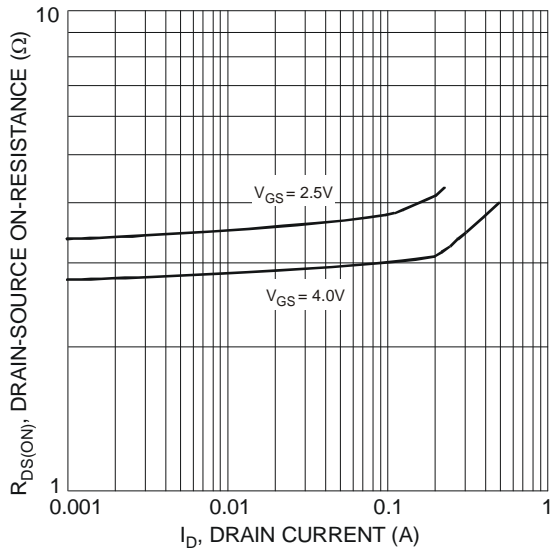


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

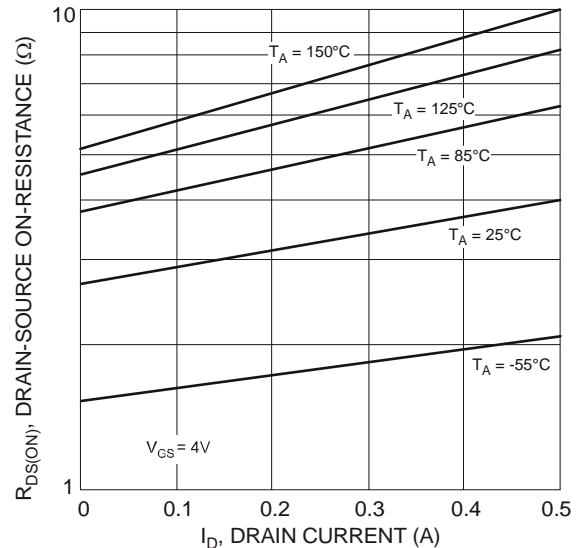


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

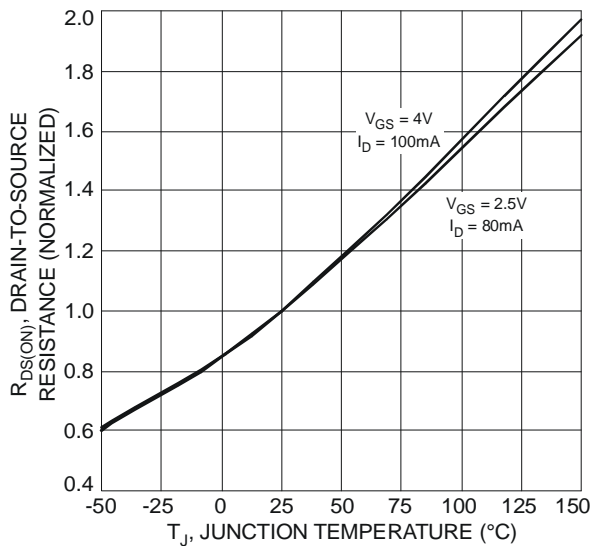


Fig. 5 On-Resistance Variation with Temperature

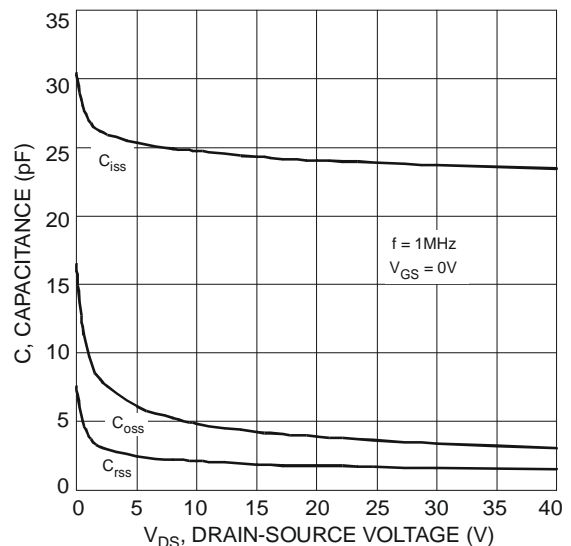


Fig. 6 Typical Capacitance

MOSFET (continued)

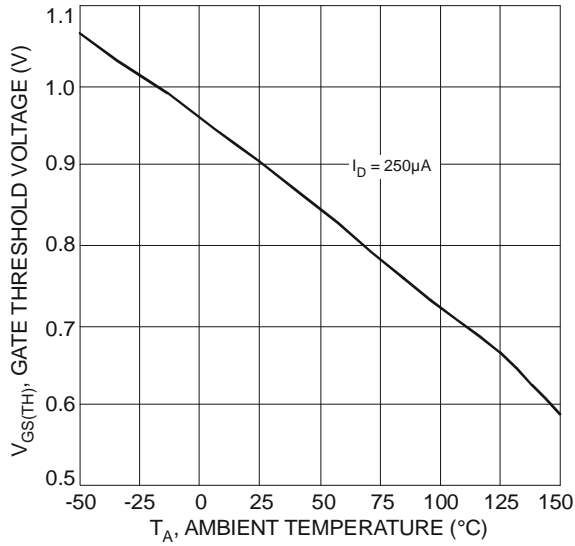


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

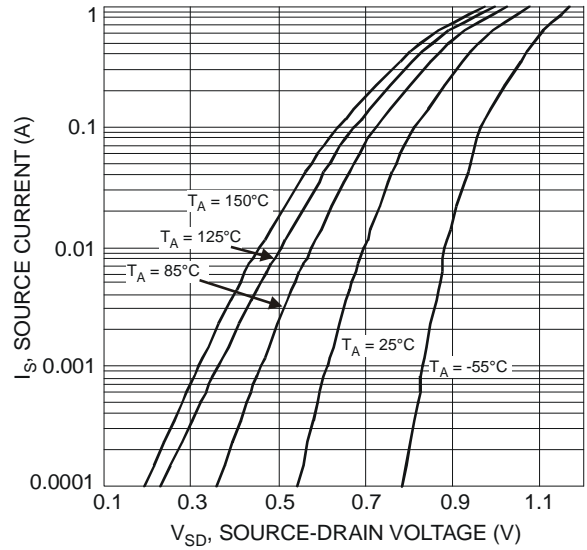


Fig. 8 Diode Forward Voltage vs. Current

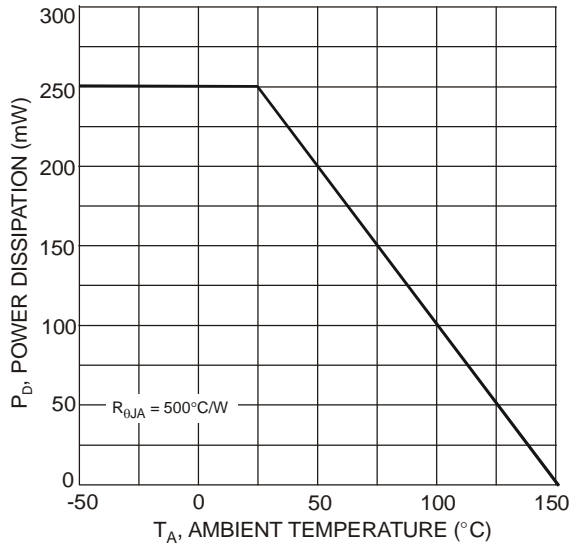


Fig. 9 Derating Curve - Total Package Power Dissipation

PNP Transistor

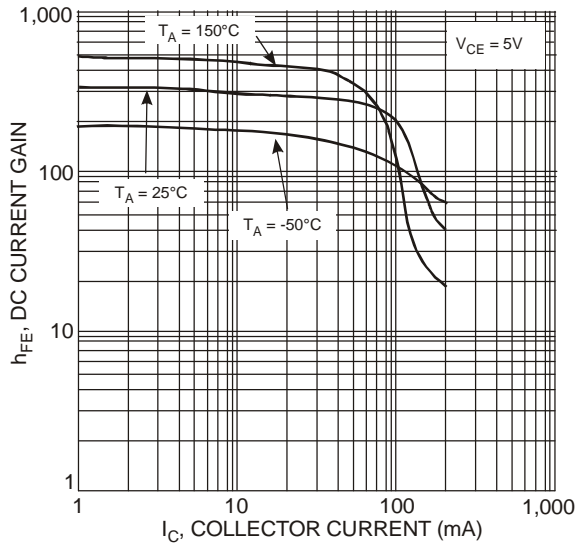


Fig. 10 Typical DC Current Gain vs. Collector Current

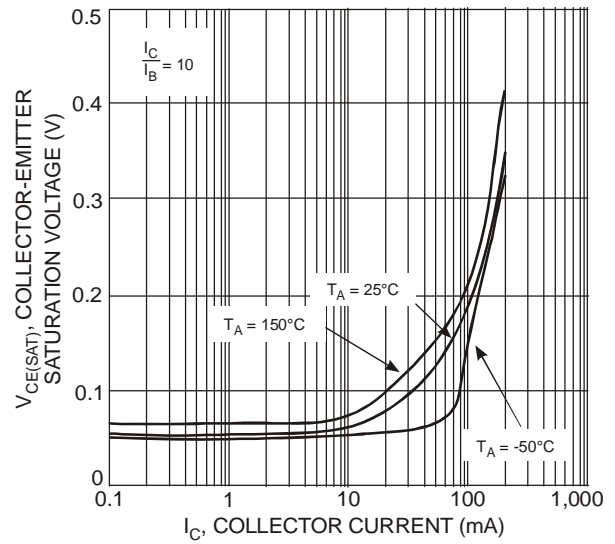


Fig. 11 Collector-Emitter Saturation Voltage vs. Collector Current

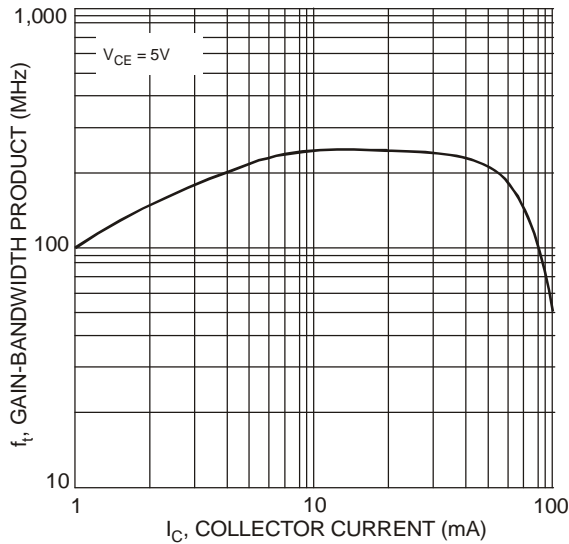


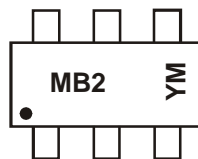
Fig. 12 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Part Number	Case	Packaging
DMB54D0UDW-7	SOT-363	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



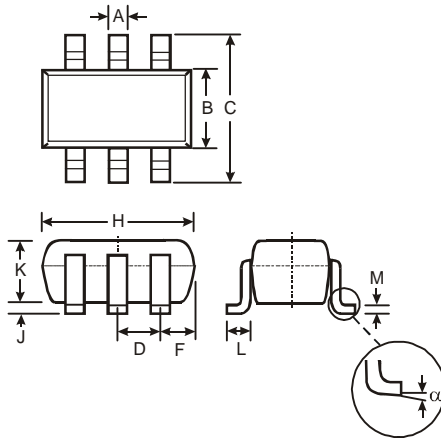
MB2 = Marking Code
YM = Date Code Marking
Y = Year (ex: V = 2008)
M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

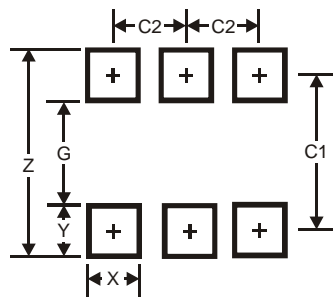
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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